

DATA SHEET

NEC

NPN SILICON RF TRANSISTOR 2SC5508

NPN SILICON RF TRANSISTOR FOR LOW-NOISE, HIGH-GAIN AMPLIFICATION FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M04)

FEATURES

- Ideal for low-noise, high-gain amplification applications
- $NF = 1.1 \text{ dB TYP.}$, $G_a = 16 \text{ dB TYP.}$ @ $V_{CE} = 2 \text{ V}$, $I_c = 5 \text{ mA}$, $f = 2 \text{ GHz}$
- Maximum available power gain: $MAG = 19 \text{ dB TYP.}$ @ $V_{CE} = 2 \text{ V}$, $I_c = 20 \text{ mA}$, $f = 2 \text{ GHz}$
- $f_T = 25 \text{ GHz}$ technology adopted
- Flat-lead 4-pin thin-type super minimold (M04) package

ORDERING INFORMATION

Part Number	Quantity	Supplying Form
2SC5508	50 pcs (Non reel)	<ul style="list-style-type: none"> • 8 mm wide embossed taping • Pin 1 (Emitter), Pin 2 (Collector) face the perforation side of the tape
2SC5508-T2	3 kpcs/reel	

Remark To order evaluation samples, contact your nearby sales office.
The unit sample quantity is 50 pcs.

ABSOLUTE MAXIMUM RATINGS ($T_A = +25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	15	V
Collector to Emitter Voltage	V_{CEO}	3.3	V
Emitter to Base Voltage	V_{EBO}	1.5	V
Collector Current	I_c	35	mA
Total Power Dissipation	P_{tot} ^{Note}	115	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +150	$^\circ\text{C}$

Note Free air

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

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Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

THERMAL RESISTANCE

Parameter	Symbol	Ratings	Unit
Junction to Case Resistance	R _{th j-c}	150	°C/W
Junction to Ambient Resistance	R _{th j-a}	650	°C/W

ELECTRICAL CHARACTERISTICS (T_A = +25 °C)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Collector Cut-off Current	I _{CBO}	V _{CB} = 5 V, I _E = 0 mA	–	–	200	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 1 V, I _C = 0 mA	–	–	200	nA
DC Current Gain	h _{FE} ^{Note 1}	V _{CE} = 2 V, I _C = 5 mA	50	70	100	–
RF Characteristics						
Gain Bandwidth Product	f _T	V _{CE} = 3 V, I _C = 30 mA, f = 2 GHz	20	25	–	GHz
Insertion Power Gain	S _{21e} ²	V _{CE} = 2 V, I _C = 20 mA, f = 2 GHz	14	17	–	dB
Noise Figure	NF	V _{CE} = 2 V, I _C = 5 mA, f = 2 GHz, Z _S = Z _{opt}	–	1.1	1.5	dB
Reverse Transfer Capacitance	C _{re} ^{Note 2}	V _{CB} = 2 V, I _E = 0 mA, f = 1 MHz	–	0.18	0.24	pF
Maximum Available Power Gain	MAG ^{Note 3}	V _{CE} = 2 V, I _C = 20 mA, f = 2 GHz	–	19	–	dB
Maximum Stable Power Gain	MSG ^{Note 4}	V _{CE} = 2 V, I _C = 20 mA, f = 2 GHz	–	20	–	dB
Gain 1 dB Compression Output Power	P _{O(1 dB)}	V _{CE} = 2 V, I _C = 20 mA ^{Note 5} , f = 2 GHz	–	11	–	dBm
3rd Order Intermodulation Distortion Output Intercept Point	OIP ₃	V _{CE} = 2 V, I _C = 20 mA ^{Note 5} , f = 2 GHz	–	22	–	dBm

- Notes**
1. Pulse measurement: PW ≤ 350 μs, Duty Cycle ≤ 2%
 2. Collector to base capacitance when the emitter grounded
 3. $MAG = \left| \frac{S_{21}}{S_{12}} \right| (K - \sqrt{K^2 - 1})$
 4. $MSG = \left| \frac{S_{21}}{S_{12}} \right|$
 5. Collector current when P_{O(1 dB)} is output

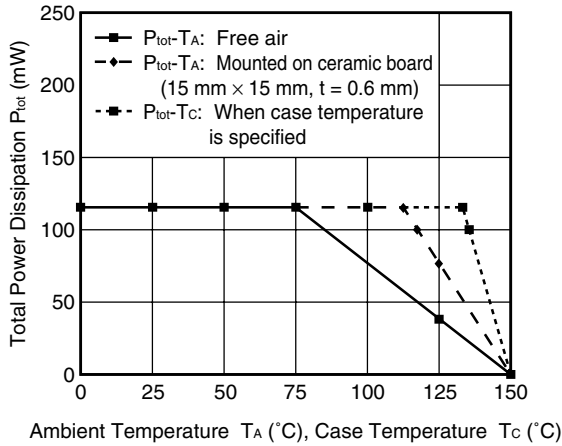
h_{FE} CLASSIFICATION

Rank	FB
Marking	T79
h _{FE} Value	50 to 100

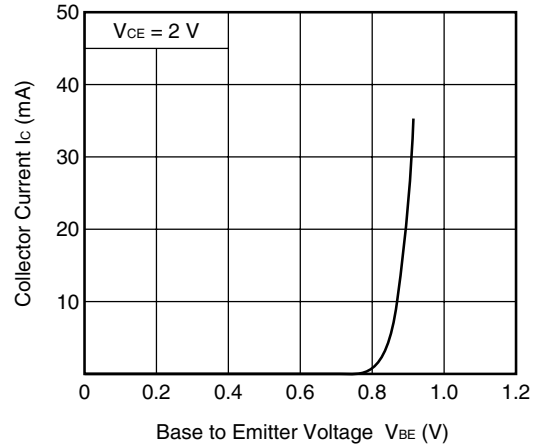
★ TYPICAL CHARACTERISTICS (T_A = +25°C, unless otherwise specified)

Thermal/DC Characteristics

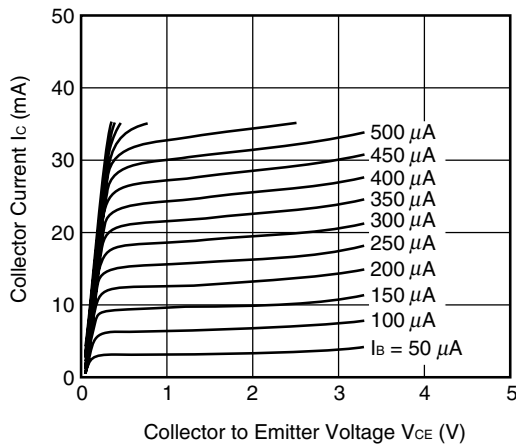
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE, CASE TEMPERATURE



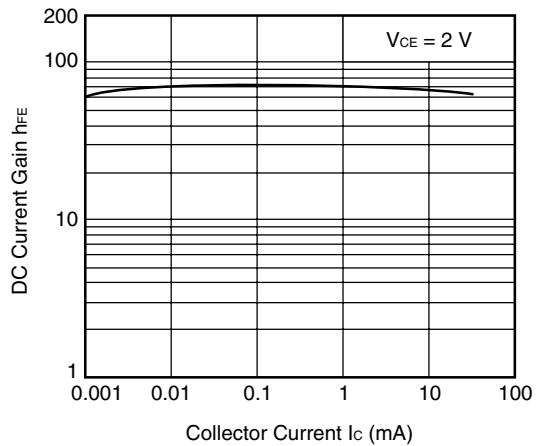
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE

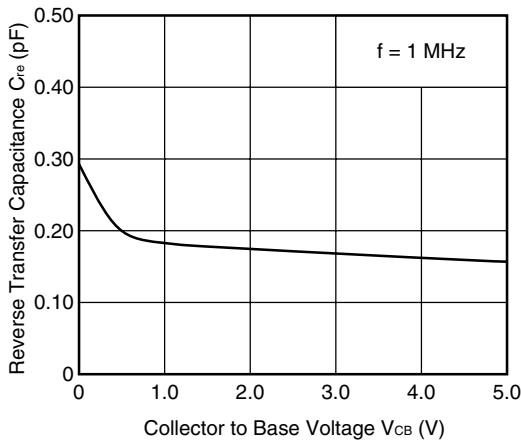


DC CURRENT GAIN vs. COLLECTOR CURRENT

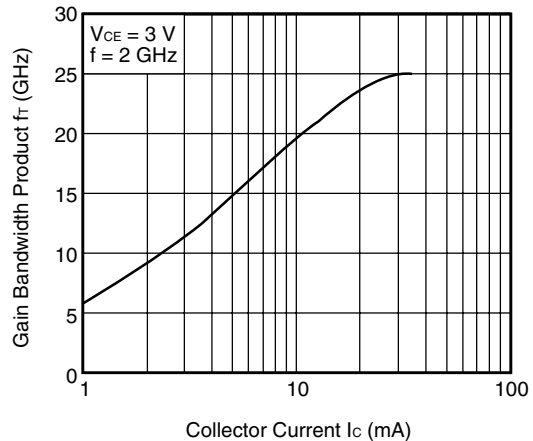


Capacitance/ f_T Characteristics

REVERSE TRANSFER CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



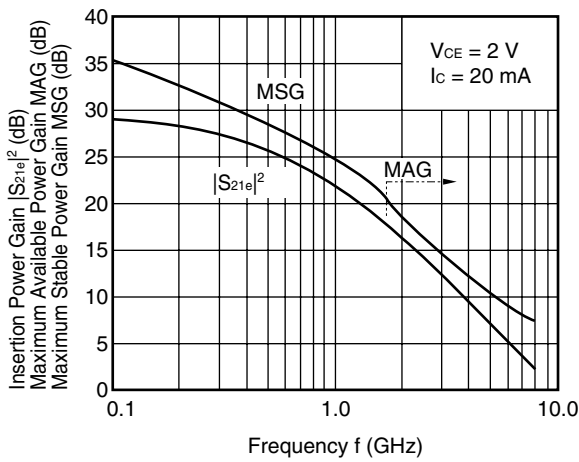
GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT



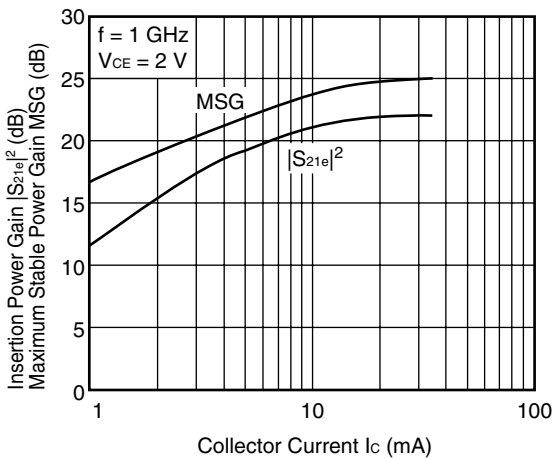
Remark The graphs indicate nominal characteristics.

Gain Characteristics

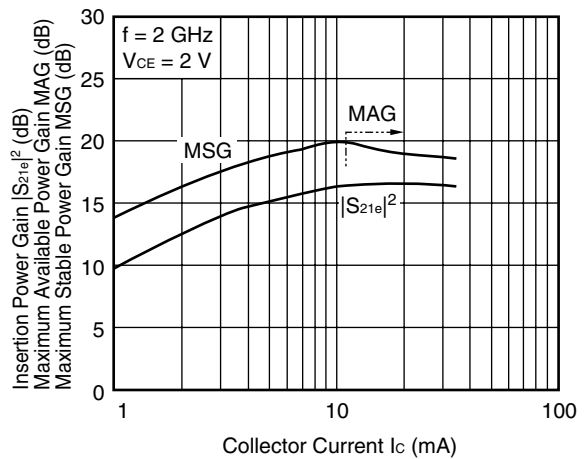
INSERTION POWER GAIN, MAG, MSG vs. FREQUENCY



INSERTION POWER GAIN, MSG vs. COLLECTOR CURRENT

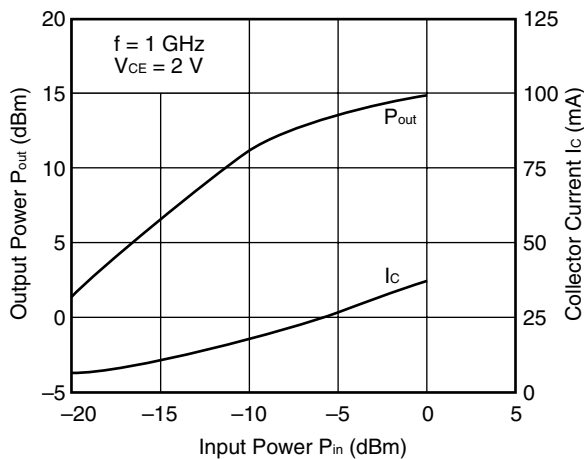


INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT

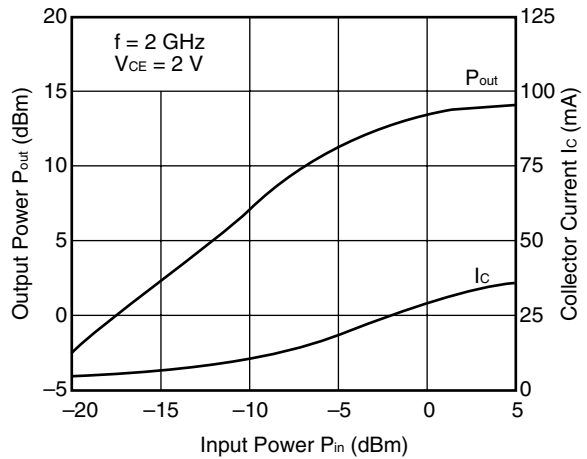


Output Characteristics

OUTPUT POWER, COLLECTOR CURRENT vs. INPUT POWER



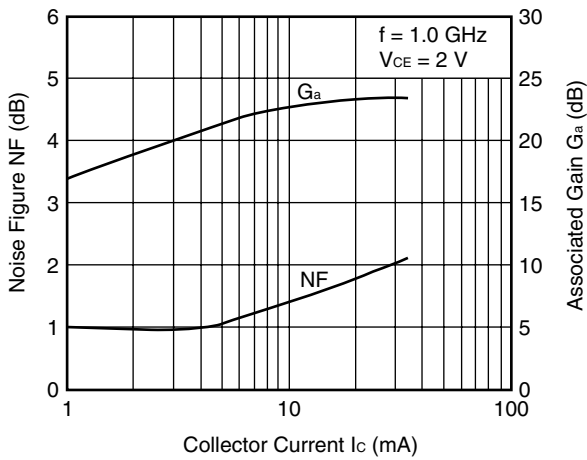
OUTPUT POWER, COLLECTOR CURRENT vs. INPUT POWER



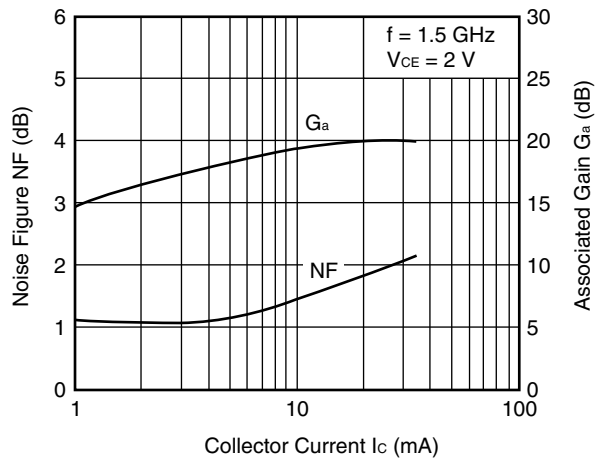
Remark The graphs indicate nominal characteristics.

Noise Characteristics

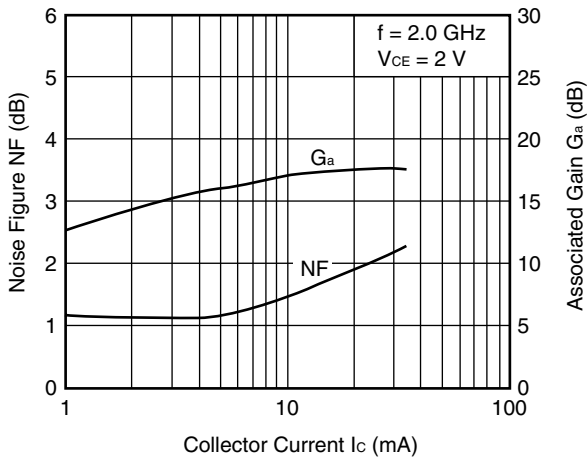
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



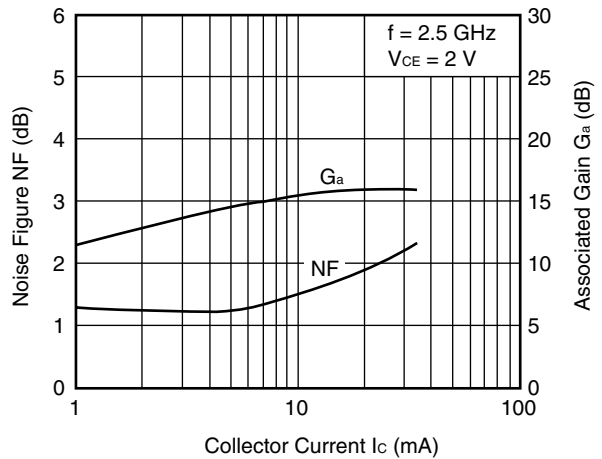
NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



Remark The graphs indicate nominal characteristics.

★ **S-PARAMETERS**

S-parameters/Noise parameters are provided on the NEC Compound Semiconductor Devices Web site in a form (S2P) that enables direct import to a microwave circuit simulator without keyboard input.

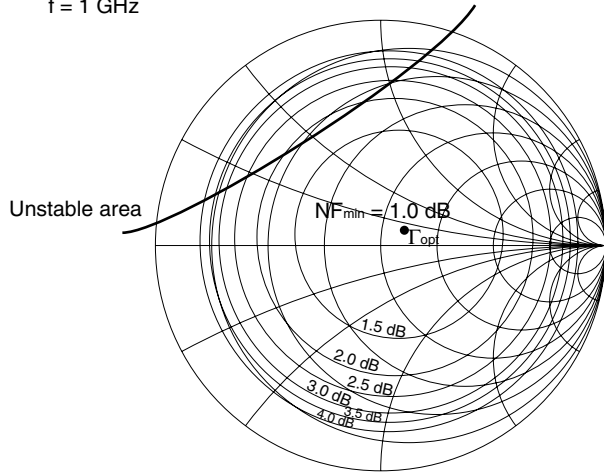
Click here to download S-parameters.

[RF and Microwave] → [Device Parameters]

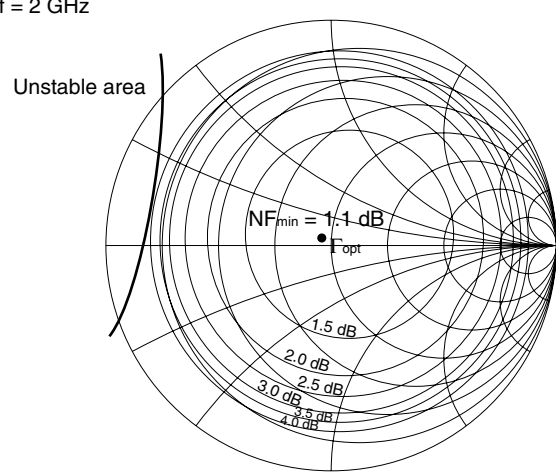
URL <http://www.ncsd.necel.com/>

EQUAL NF CIRCLE

$V_{CE} = 2\text{ V}$
 $I_C = 5\text{ mA}$
 $f = 1\text{ GHz}$



$V_{CE} = 2\text{ V}$
 $I_C = 5\text{ mA}$
 $f = 2\text{ GHz}$



NOISE PARAMETERS

$V_{CE} = 2\text{ V}$, $I_c = 3\text{ mA}$

f (GHz)	NF _{min} (dB)	G _a (dB)	Γ _{opt}		Rn/50
			MAG.	ANG.	
0.8	0.78	21.4	0.26	31.7	0.17
0.9	0.80	20.7	0.26	32.7	0.17
1.0	0.82	20.0	0.26	34.7	0.17
1.5	0.93	17.0	0.23	57.0	0.16
1.8	1.00	15.6	0.20	78.0	0.14
1.9	1.02	15.2	0.19	86.0	0.14
2.0	1.04	14.8	0.19	94.2	0.13
2.5	1.15	13.5	0.20	138.3	0.10

$V_{CE} = 2\text{ V}$, $I_c = 5\text{ mA}$

f (GHz)	NF _{min} (dB)	G _a (dB)	Γ _{opt}		Rn/50
			MAG.	ANG.	
0.8	0.93	22.5	0.12	28.1	0.15
0.9	0.94	21.8	0.12	28.8	0.15
1.0	0.96	21.1	0.12	31.7	0.15
1.5	1.03	18.1	0.09	71.1	0.14
1.8	1.07	16.7	0.08	106.2	0.13
1.9	1.09	16.3	0.08	118.5	0.13
2.0	1.10	15.9	0.08	130.5	0.12
2.5	1.17	14.3	0.14	-179.7	0.11

$V_{CE} = 2\text{ V}$, $I_c = 10\text{ mA}$

f (GHz)	NF _{min} (dB)	G _a (dB)	Γ _{opt}		Rn/50
			MAG.	ANG.	
0.8	1.28	23.7	0.07	-159.4	0.13
0.9	1.29	23.0	0.07	-157.5	0.13
1.0	1.30	22.3	0.08	-155.7	0.13
1.5	1.37	19.3	0.13	-149.2	0.13
1.8	1.41	17.8	0.16	-146.1	0.13
1.9	1.43	17.3	0.17	-145.0	0.13
2.0	1.44	16.9	0.19	-143.9	0.13
2.5	1.51	15.3	0.25	-136.7	0.13

$V_{CE} = 2\text{ V}$, $I_c = 20\text{ mA}$

f (GHz)	NF _{min} (dB)	G _a (dB)	Γ _{opt}		Rn/50
			MAG.	ANG.	
0.8	1.59	24.5	0.26	-158.1	0.12
0.9	1.61	23.7	0.26	-155.5	0.13
1.0	1.63	23.0	0.27	-153.1	0.13
1.5	1.72	19.9	0.30	-142.6	0.14
1.8	1.78	18.3	0.33	-137.3	0.15
1.9	1.79	17.9	0.34	-135.7	0.06
2.0	1.81	17.5	0.35	-134.1	0.16
2.5	1.90	15.8	0.40	-126.5	0.18

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M8E 00.4-0110

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